## **EUROPEAN PATENT OFFICE**

Patent Abstracts of Japan

**PUBLICATION NUMBER** 

2003068643

**PUBLICATION DATE** 

07-03-03

**APPLICATION DATE** 

23-08-01

**APPLICATION NUMBER** 

2001252393

APPLICANT :

JAPAN ADVANCED INST OF SCIENCE

& TECHNOLOGY HOKURIKU;

INVENTOR: IMAMORI KENSAKU;

INT.CL.

H01L 21/20 H01L 21/205 H01L 31/04 //

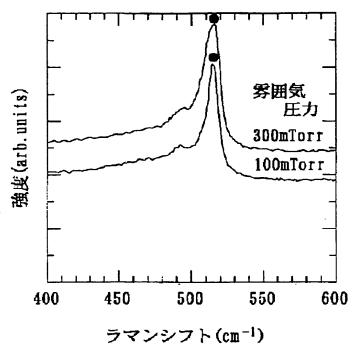
C23C 16/24 C23C 16/56

TITLE

METHOD FOR MANUFACTURING

CRYSTALLINE SILICON FILM AND

SOLAR CELL



ABSTRACT :

PROBLEM TO BE SOLVED: To provide a novel method for manufacturing a crystalline

silicon film on an oxide transparent electrode, without reducing transmittivity.

SOLUTION: An amorphous silicon film is formed on an oxide transparent electrode. Atomic hydrogen is irradiated on the amorphous silicon at an atmospheric pressure of

preferably 1 to 1,000 mTorr, so as to crystalline the amorphous silicon film.

COPYRIGHT: (C)2003,JPO